

ABSTRACT OF THE DISCLOSURE

The invention provides a technology capable of preventing an excessive leak current in a pn junction of a photodiode. The n-type region of a photodiode is separated from a device
5 isolating part and a p-type region of relatively high concentration is formed in such a way as to be in contact with the n-type region to reduce the effect which an interface state between the semiconductor substrate and the device isolating part or a stress caused by the crystal mismatching of a silicon
10 single crystal constructing the semiconductor substrate produces on a depletion layer produced in the boundary between the n-type region and the p-type region of the photodiode, thereby reducing the leak current in the pn junction of the photodiode.